



Docket No. 740756-2119

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Hisashi OHTANI et al.

Serial No. 09/550,598

Filed: April 17, 2000

For: SEMICONDUCTOR DEVICE AND
PROCESS FOR PRODUCING THE
SAME

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TC 2500 MAIL ROOM

Group Art Unit: 2814

Examiner: P. Cao

Date: January 11, 2002

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CERTIFICATE OF MAILING

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D.C. 20231, on 1/11/02

Eugene J. Cantrell
Eugene J. Cantrell

AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the non-final Office Action mailed October 11, 2001, please amend the
above identified application as follows.

09/25/2002 SERIAL 00000001 192380 09550598
01 FC:102 522.00 CH

IN THE CLAIMS:

Please cancel claims 13, 16, 17 and 19 without prejudice to or disclaimer of the subject
matter disclosed therein.

Please amend claims 1-5, 14, 15, 18, and 20-26 as follows. Claims 1-5, 14, 15, 18, and
20-26 are presented below in their amended form. The amendments to the above-noted claims
are outlined in an Attachment to the Amendment using the conventional indication method of
bracketing and underlining.

1. (Amended) A method for producing a semiconductor device comprising:
- forming a first conductive layer;
 - forming an insulating layer comprising an organic resin over said first conductive layer;
 - forming an opening in said insulating layer to expose said first conductive layer at a
bottom of said opening;

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